Supplementary material

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Plot

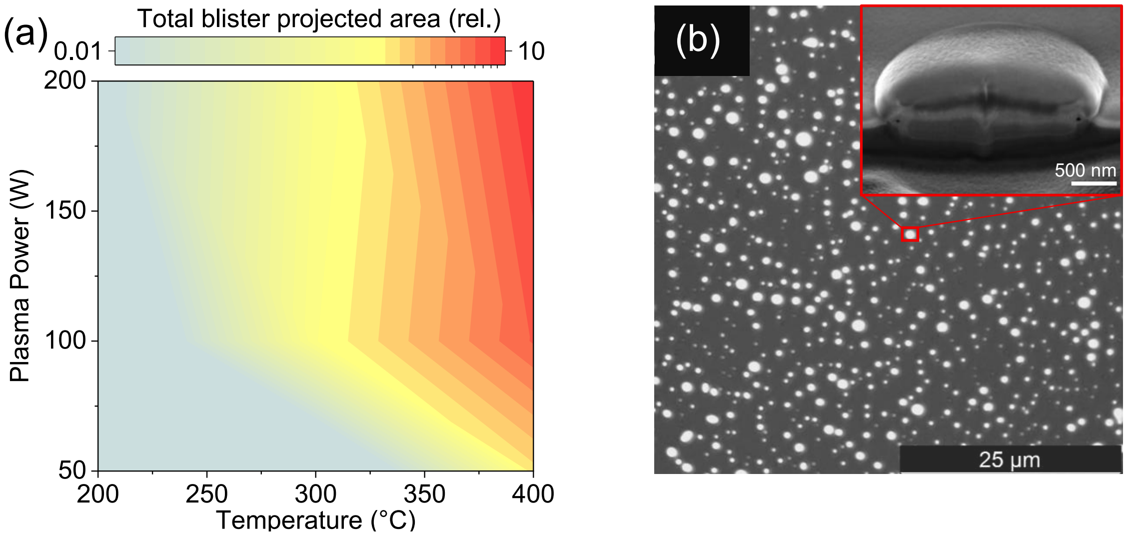

Figure 1: ***(a)*** *Contour map of the relative total blister projected area (%) as a function of chuck temperature and NH_3 plasma power. The relative total blister projected area is defined as the sum of the projected (top-view) areas of all blisters, normalized by the AFM scan area (2x2 µm²) and represents the fraction of the surface covered by blisters.* ***(b)*** *Optical microscope image of the AlN film deposited at 400 °C and 200 W, showing blister formation. An inset shows a magnified SEM-FIB cross-section of a representative blister.*